

2SC5419

Silicon NPN triple diffusion planar type

For low-frequency output amplification

■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- High transition frequency f_T
- Allowing supply with the radial taping

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 300 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 300 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 7 | V |
| Collector current | I_C | 70 | mA |
| Peak collector current | I_{CP} | 100 | mA |
| Collector power dissipation * | P_C | 1 | W |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Note) *: Copper plate at the collector is more than 1 cm^2 in area, 1.7 mm in thickness

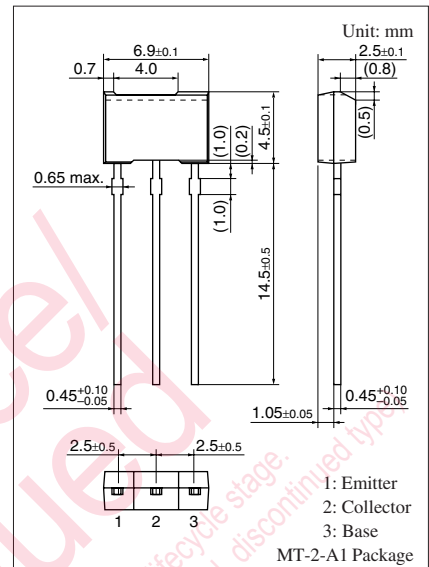
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

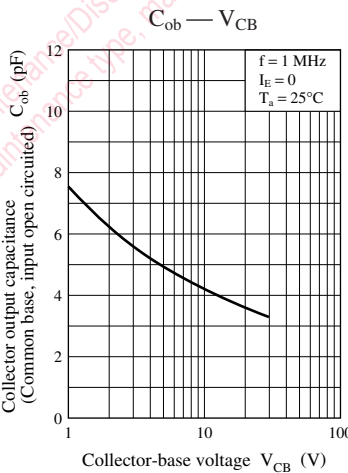
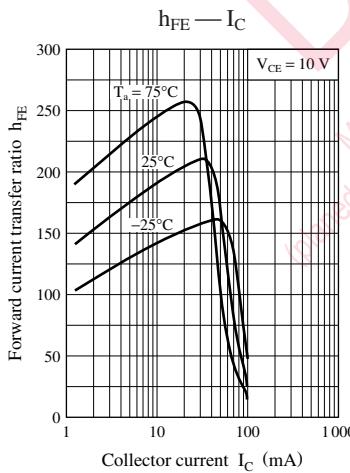
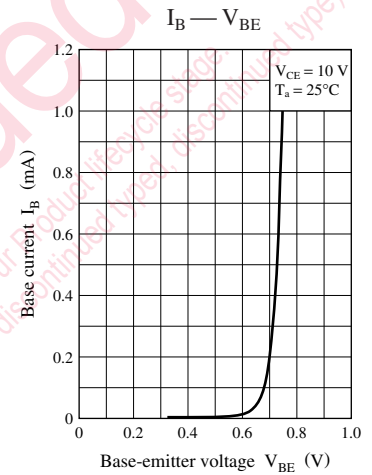
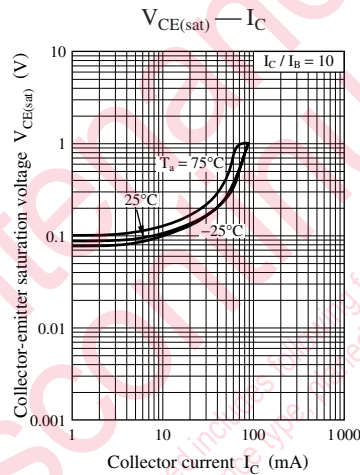
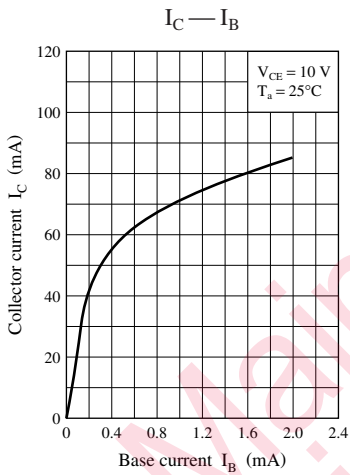
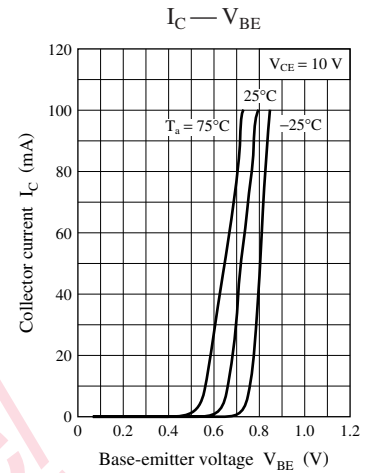
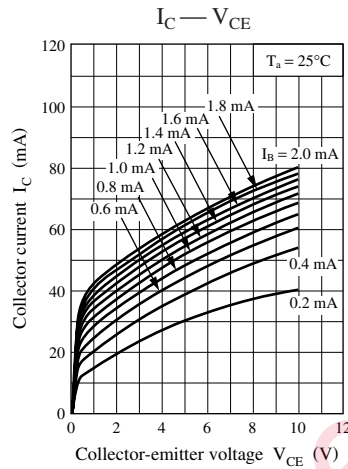
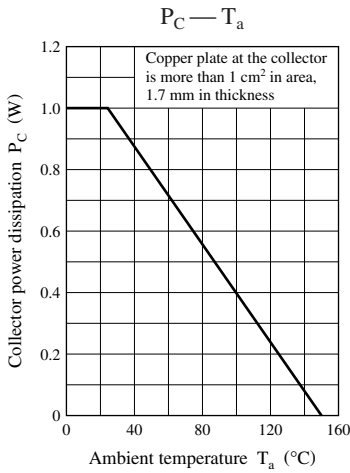
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|---------------|---|-----|-----|-----|---------------|
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 100\ \mu\text{A}$, $I_B = 0$ | 300 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 1\ \mu\text{A}$, $I_C = 0$ | 7 | | | V |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 120\text{ V}$, $I_B = 0$ | | | 1 | μA |
| Forward current transfer ratio * | h_{FE} | $V_{CE} = 10\text{ V}$, $I_C = 5\text{ mA}$ | 30 | | 220 | — |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$ | | | 1.2 | V |
| Transition frequency | f_T | $V_{CB} = 10\text{ V}$, $I_E = -10\text{ mA}$, $f = 200\text{ MHz}$ | 50 | | | MHz |
| Collector output capacitance (Common base, input open circuited) | C_{ob} | $V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$ | | | 10 | pF |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

| Rank | P | Q | R |
|----------|-----------|-----------|------------|
| h_{FE} | 30 to 100 | 60 to 150 | 100 to 220 |





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